Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	403	349/152.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/25 15:40
S3	38	"349"/\$.ccls. and morishita.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 12:16
S4	283	349/152.ccls. and terminal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 08:48
S5	27	349/152.ccls. and terminal near circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:48
S6	247	S2 and transparent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:26
S7	104	S2 and transparent near conductive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:26
S8	116	S2 and transparent near conduct\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 16:37
S9	148	"349"/\$.ccls. and terminal same transparent adj conduct\$5 same resistance	US-PGPÜB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 13:18

S17	46	"349"/\$.ccls. and "high resistance" same "low resistance" same	US-PGPUB; USPAT;	OR	ON	2005/07/20 15:12
		conductive	USOCR; EPO; JPO; DERWENT; IBM_TDB			
S18	1576	"349"/\$.ccls. and circuit same adjacent same circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 15:12
S19	200	"349"/\$.ccls. and circuit same adjacent near2 circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 15:12
S21	31	"349"/\$.ccls. and circuit same "adjacent circuit"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 15:13
S22	320	349/152.ccls. and circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/20 15:20
S26	28	349/152.ccls. and external adj terminal same terminal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/07/22 09:23
S27	39	"349"/\$.ccls. and conductive adj particles same (level equal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 10:12
S28	12	"349"/\$.ccls. and conductive adj (material film layer particle) same connect\$4 adj reliability	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR _.	ON	2005/07/21 09:56

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S29	95	"349"/\$.ccls. and conductive adj particles same (level equal even uneven)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 10:13
S30	. 7	"349"/\$.ccls. and high adj resistance adj conductive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:40
S31	121	"349"/\$.ccls. and resistance adj conductive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:45
S32	1483	"349"/\$.ccls. and conductive same (CR chromium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:51
S33	223	"349"/\$.ccls. and conductive same (CR chromium) same terminal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:56
534	299	"349"/\$.ccls. and conductive same (CR chromium) same high	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:57
S35	2	"349"/\$.ccls. and (CR chromium) same high near resistance near conductive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/07/22 09:58
S36	13	"349"/\$.ccls. and (CR chromium) same low near resistance near conductive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON.	2005/07/22 10:06

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S37 _.	1	"349"/\$.ccls. and (TI ta mo w ni titanium tantalum molybdenum tungsten nickel) same high near resistance near conductive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 10:07
538	107	"349"/\$.ccls. and (TI ta mo w ni titanium tantalum molybdenum tungsten nickel) same high near resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 10:15
S39	0	"349"/\$.ccls. and (TI ta mo w ni titanium tantalum molybdenum tungsten nickel) same high near resistance same connection near reliability	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 10:15
S40		"349"/\$.ccls. and (TI ta mo w ni titanium tantalum molybdenum tungsten nickel) same high near resistance same connection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 10:16
S43	1937	349/149-152.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 11:50
S44	11	("3591839" "4283118" "4336551" "4826297").PN. OR ("5726726"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON ·	2006/05/01 10:09
S45	4	("4139278").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/01 11:50
S46	1938	349/149-152.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/25 13:23
S47	318	349/149-152.ccls. and terminal and pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:30

S54	1869	349/149-151.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/25 13:23
S55	232	349/152.ccls. and (Cr Ti Ta Mo W Ni chromium titanium tantalum molybdenum tungsten nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/10/25 17:29
S58	173	349/151.ccls. and (Cr Ti Ta Mo W Ni chromium titanium tantalum molybdenum tungsten nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/25 17:30
S59	218312	(terminal).clm.	USPAT	OR	ON	2006/10/25 18:09
S60	68351	(driver adj circuit drive adj circuit IC chip).clm.	USPAT	OR	ON	2006/10/25 18:10
S61	465411	(high\$4).clm.	USPAT	OR	ON	2006/10/25 18:11
S62	751321	(low\$4).clm.	USPAT	OR	ON	2006/10/25 18:11
S63	1978	S59 and S60 and S61 and S62	USPAT	OR	ON	2006/10/25 18:11
S64	360489	(conduct\$4).clm.	USPAT	OR	ON	2006/10/25 18:11
S65	649	(ACF anisotropic adj conductive). clm.	USPAT	OR	ON	2006/10/25 18:11
S66	5	S59 and S60 and S61 and S62 and S64 and S65	USPAT	OR	ON	2006/10/25 18:12